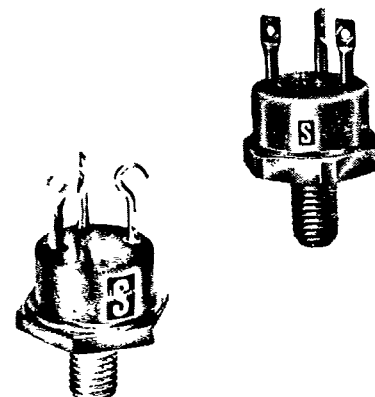


RADIATION RESISTANT NPN SILICON POWER TRANSISTORS**BR100E BR100F* BR101E BR101F*****NPN SILICON POWER TRANSISTORS
RADIATION RESISTANT****10 AMPERES****FEATURES**

HIGH POWER
 RADIATION EXPOSURE LEVEL TO $3 \times 10^{14} \text{n/Cm}^2$
 TOTAL NEUTRON FLUX EQUIVALENT TO 1 MEV

APPLICATIONS

POWER AMPLIFIER
 RADIATION ENVIRONMENTS
 ULTRA HIGH FREQUENCY

**T0-61/T0-61/I**

*T0-61/I

ABSOLUTE MAXIMUM RATINGS

		BR100E BR100F*	BR101E BR101F*
V_{CB0}	COLLECTOR-BASE VOLTAGE	75 V	90 V
V_{CE0}	COLLECTOR-EMITTER VOLTAGE	60 V	80 V
V_{EB0}	EMITTER-BASE VOLTAGE	5 V	5 V
I_C	CONTINUOUS COLLECTOR CURRENT	10 A	10 A
I_B	CONTINUOUS BASE CURRENT	2 A	2 A
T_J	OPERATING JUNCTION TEMPERATURE	_____ -65°C to +200°C _____	
T_{stg}	STORAGE TEMPERATURE	_____ -65°C to +200°C _____	
$R_{\theta JC}$	THERMAL RESISTANCE, JUNCTION TO CASE	5.0°C/W	
P_D	POWER DISSIPATION (25°C)	35W	

3-85-2R

RADIATION RESISTANT NPN SILICON POWER TRANSISTORS**BR100E BR100F* BR101E BR101F***

SOLITRON DEVICES INC

ELECTRICAL CHARACTERISTICS (T_C = 25°C UNLESS OTHERWISE NOTED)

CHARACTERISTICS	SYMBOL	MIN.	MAX.	UNITS
COLLECTOR-BASE BREAKDOWN VOLTAGE (I _{CB0} = 1.0mA) BR100E, BR100F (I _{CB0} = 1.0mA) BR101E, BR101F (I _{CB0} = 1.0mA, Note 2) BR100E, BR100F (I _{CB0} = 1.0mA, Note 2) BR101E, BR101F	V _{CB0}	75 90 75 90		V V V V
COLLECTOR-EMITTER SUSTAINING VOLTAGE ⁽¹⁾ (I _{CE0} = 50mA) BR100E, BR100F (I _{CE0} = 50mA) BR101E, BR101F (I _{CE0} = 50mA, Note 2) BR100E, BR100F (I _{CE0} = 50mA, Note 2) BR101E, BR101F	V _{CE0}	60 80 80 100		V V V V
EMITTER-BASE VOLTAGE (I _{EB0} = 1.0mA) (I _{EB0} = 1.0mA, Note 2)	V _{EB0}	5.0 5.0		V V
COLLECTOR CUTOFF CURRENT (V _{CB} = 50V) (V _{CB} = 50V, Note 2)	I _{CB0}		0.1 0.1	mA mA
EMITTER CUTOFF CURRENT (V _{EB} = 3.0V) (V _{EB} = 3.0V, Note 2)	I _{EB0}		0.1 0.1	mA mA
DC CURRENT GAIN (1) (V _{CE} = 5.0V, I _C = 0.5A) BR100E, BR100F (V _{CE} = 5.0V, I _C = 2.0A) BR100E, BR100F (V _{CE} = 5.0V, I _C = 5.0A) BR100E, BR100F (V _{CE} = 5.0V, I _C = 0.5A) BR101E, BR101F (V _{CE} = 5.0V, I _C = 2.0A) BR101E, BR101F (V _{CE} = 5.0V, I _C = 5.0A) BR101E, BR101F (V _{CE} = 5.0V, I _C = 0.5A, Note 2) BR100E, BR100F (V _{CE} = 5.0V, I _C = 2.0A, Note 2) BR100E, BR100F (V _{CE} = 5.0V, I _C = 5.0A, Note 2) BR100E, BR100F (V _{CE} = 5.0V, I _C = 0.5A, Note 2) BR101E, BR101F (V _{CE} = 5.0V, I _C = 2.0A, Note 2) BR101E, BR101F (V _{CE} = 5.0V, I _C = 5.0A, Note 2) BR101E, BR101F	h _{FE}	60 75 25 45 70 12 15 15 5 20 15 5		
COLLECTOR-EMITTER SATURATION VOLTAGE ⁽¹⁾ (I _C = 2.0A, I _B = 0.4A) (I _C = 3.0A, I _B = 0.3A) (I _C = 2.0A, I _B = 0.4A, Note 2) BR100E, BR100F (I _C = 2.0A, I _B = 0.4A, Note 2) BR101E, BR101F	V _{CE(sat)}		0.3 1.5 2.0 3.0	V V V V
OUTPUT CAPACITANCE (V _{CB} = 30V, f = 1.0 MHZ)	C _{obo}		50	pF
MAGNITUDE OF SMALL SIGNAL GAIN (V _{CE} = 5.0V, I _C = 1.0A, f = 10MHZ)	[h _{FE}]	15		
For typical curves, soar, pulsed operation, Etc. see 2N5529 2N5530 2N5533 2N5534.				

(1): Pulsed 300μsec, Duty Cycle ≤ 2%

NOTE 2: After exposure, 1 × 10¹⁴ n/Cm², Flux 1 MEV.